

General Description

The WSK250N03 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSK250N03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

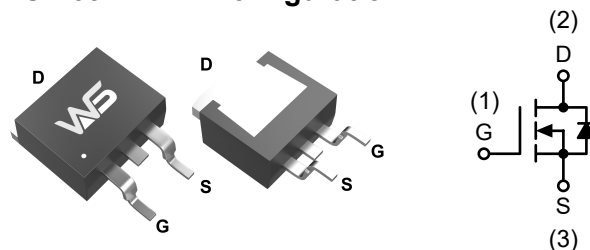
Product Summary

BVDSS	RDSON	ID
30V	1.8mΩ	250A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System

TO-263-2L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	250	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	180	A
I_{DM}	Pulsed Drain Current ²	1000	A
EAS	Single Pulse Avalanche Energy ³	600	mJ
I_{AS}	Avalanche Current	200	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ³	200	W
$P_D@T_C=100^\circ\text{C}$	Total Power Dissipation ³	120	W
T_{STG}	Storage Temperature Range	-55 to 170	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.098	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =145A	---	1.8	2.5	mΩ
		V _{GS} =4.5V, I _D =145A	---	2.5	3.5	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1	1.8	3	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-6.57	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	2	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	28	---	---	S
Q _g	Total Gate Charge (10V)	V _{DS} =20V, V _{GS} =10V, I _D =120A	---	232	---	nC
Q _{gs}	Gate-Source Charge		---	26	---	
Q _{gd}	Gate-Drain Charge		---	59	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =6Ω I _D =145A, R _L =30Ω	---	50	---	ns
T _r	Rise Time		---	111	---	
T _{d(off)}	Turn-Off Delay Time		---	88	---	
T _f	Fall Time		---	74	---	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	---	10600	---	pF
C _{oss}	Output Capacitance		---	1156	---	
C _{rss}	Reverse Transfer Capacitance		---	732	---	

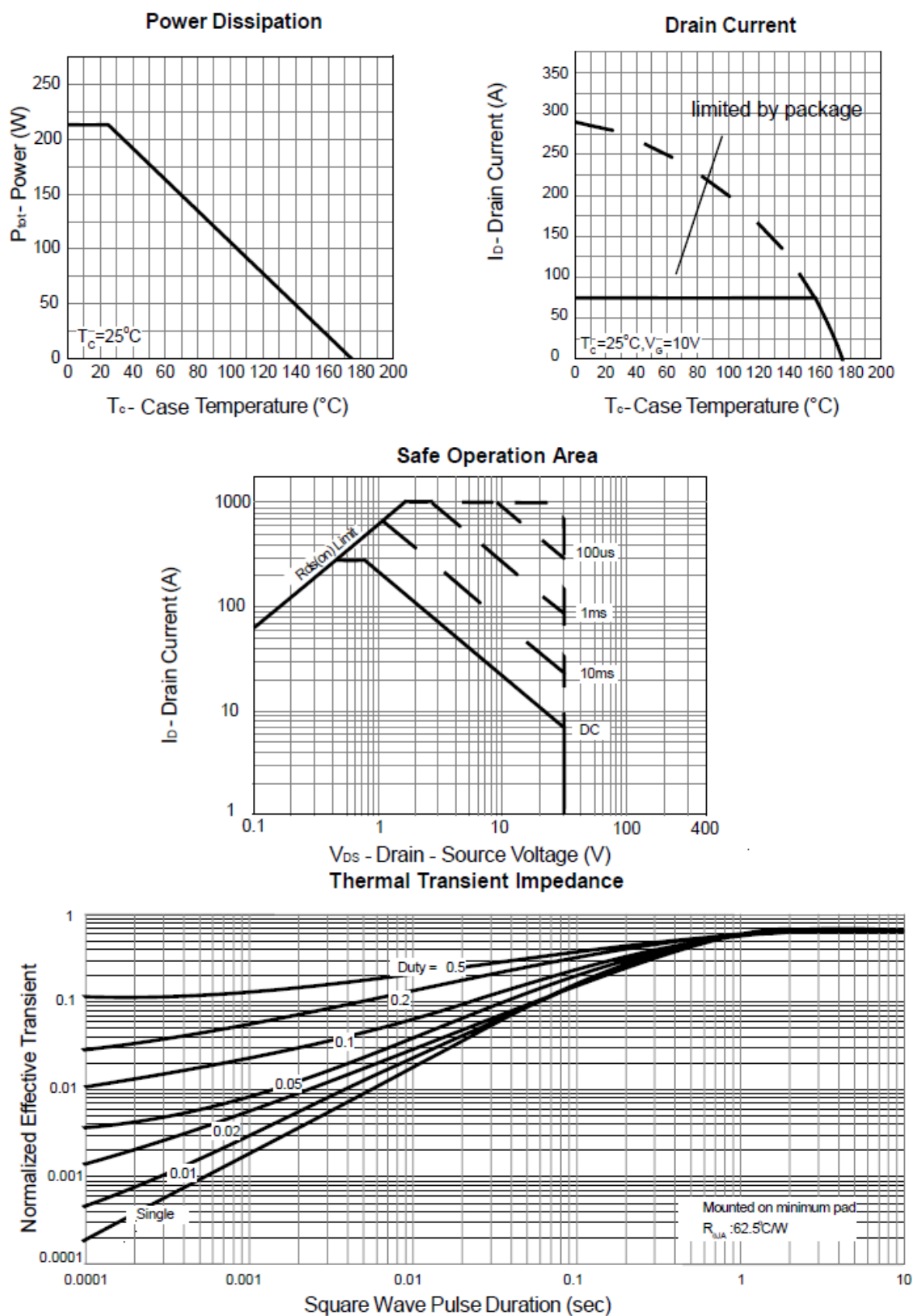
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	250	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	300	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

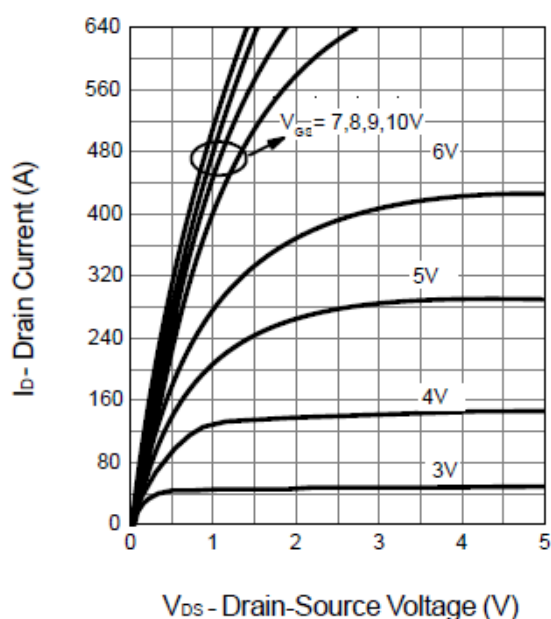
Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, t≤10sec.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.5mH, I_{AS}=20A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

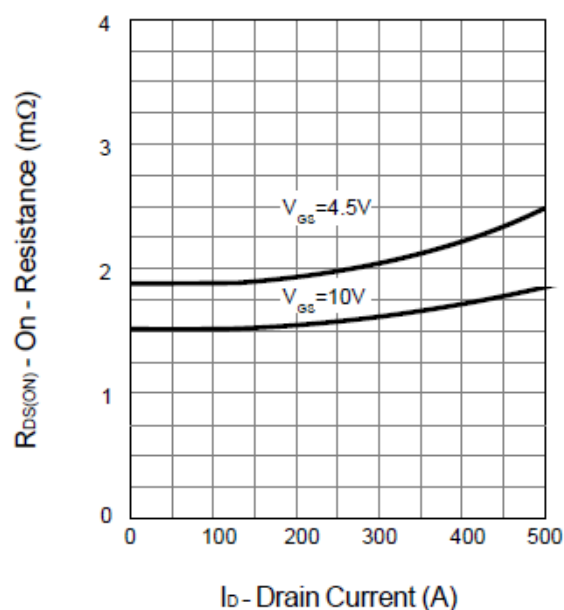
Typical Characteristics



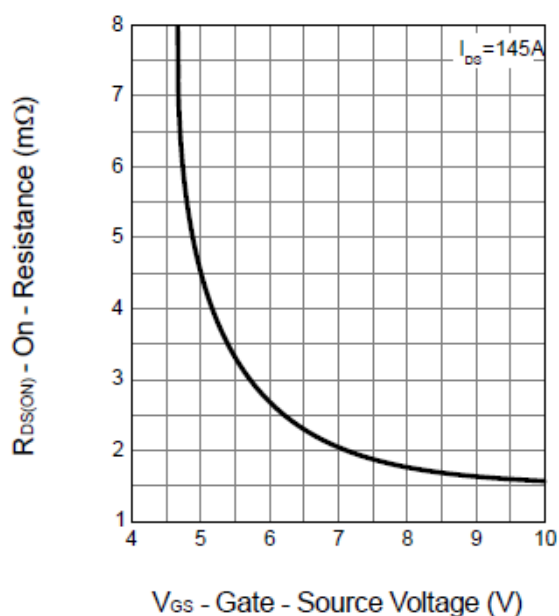
Output Characteristics



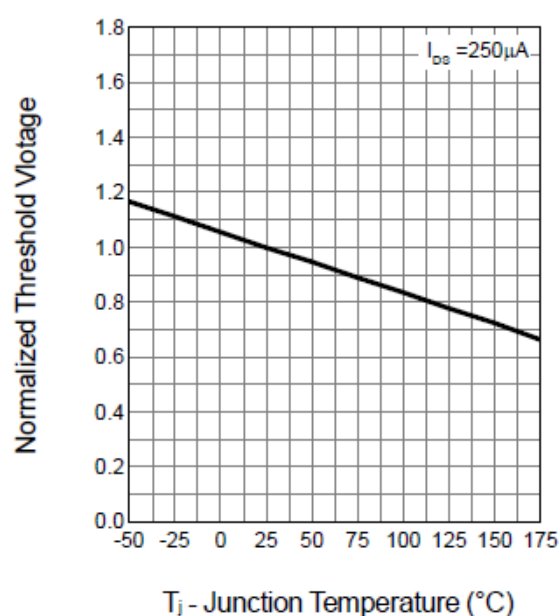
Drain-Source On Resistance



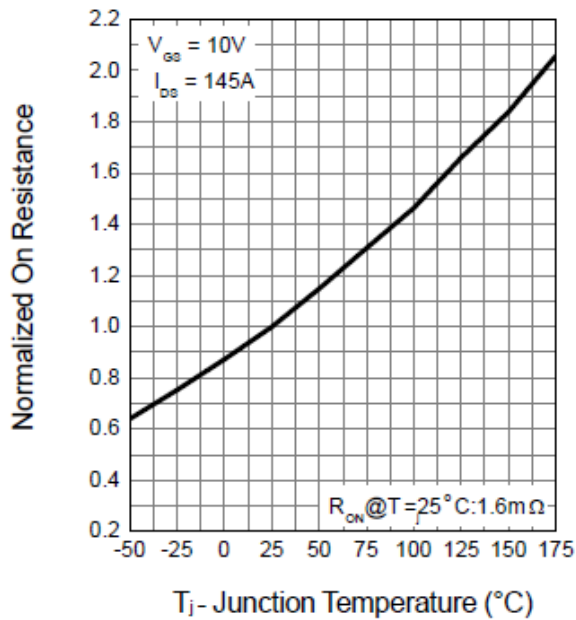
Drain-Source On Resistance



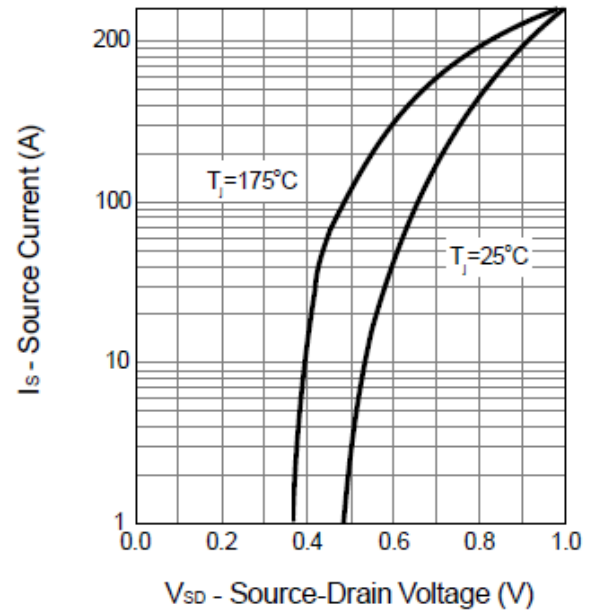
Gate Threshold Voltage



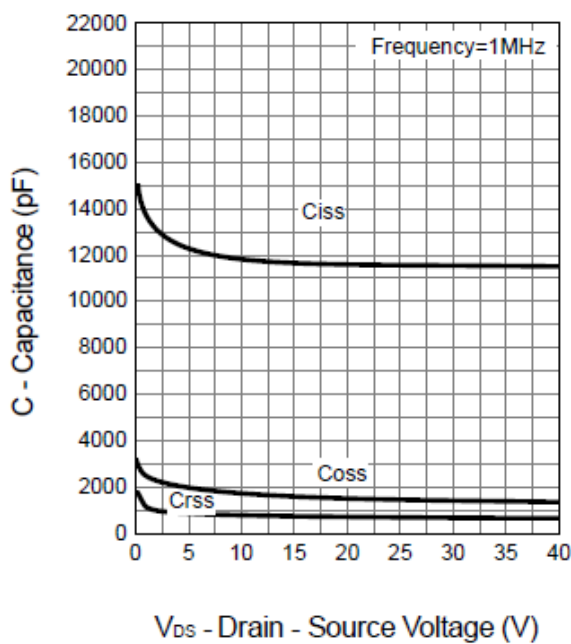
Drain-Source On Resistance



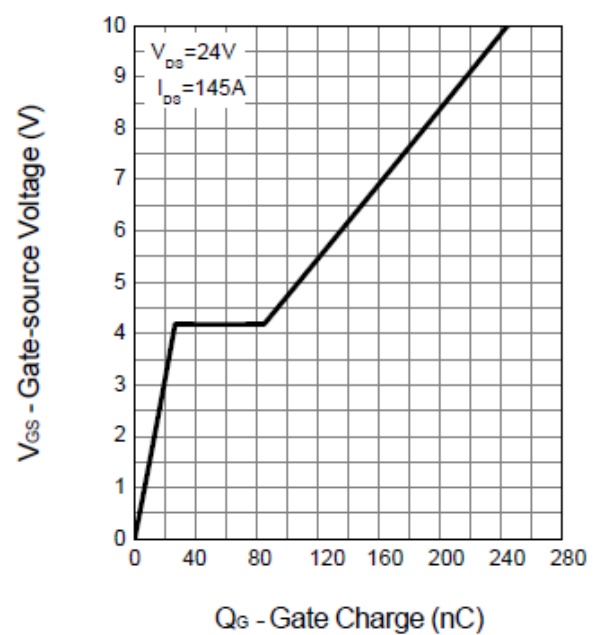
Source-Drain Diode Forward



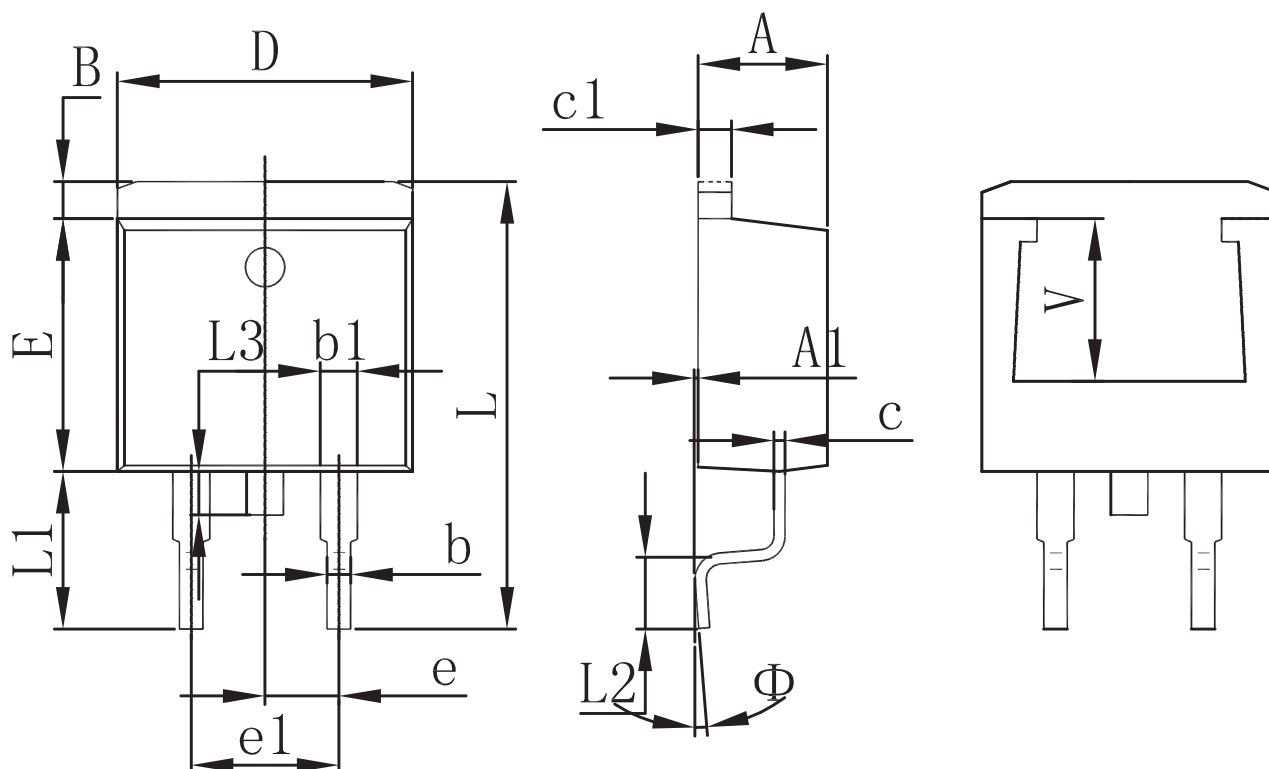
Capacitance



Gate Charge



Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
Φ	0°	8°	0°	8°
V	5.600 REF.		0.220REF.	

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